

# A Deterministic Solver for a Hybrid Quantum-Classical Transport Model in NanoMOSFETs

J. A. Carrillo

in collaboration with

N. BenAbdallah, M.J. Cáceres and F. Vecil  
(preprint 2008)

ICREA - Universitat Autònoma de Barcelona

IPAM, Los Angeles, April 1st 2009

# Outline

- 1 Introduction
  - Introduction
- 2 NanoMOSFET
  - Geometry
  - Mathematical model
- 3 NM: Kinetic Equations
  - Splitting techniques
  - PWENO interpolations
  - Benchmark tests
- 4 NM: Schrödinger-Poisson
  - Newton-Raphson Algorithms
  - Solvers for Schrödinger and Poisson
- 5 Experiments
  - Results

# Outline

- 1 Introduction
  - Introduction
- 2 NanoMOSFET
  - Geometry
  - Mathematical model
- 3 NM: Kinetic Equations
  - Splitting techniques
  - PWENO interpolations
  - Benchmark tests
- 4 NM: Schrödinger-Poisson
  - Newton-Raphson Algorithms
  - Solvers for Schrödinger and Poisson
- 5 Experiments
  - Results

# Main Objective

The goal of this work is a contribution to the numerical simulation of kinetic models for nowadays transistors.

Here we sketch the typical architecture of a **MOSFET**.

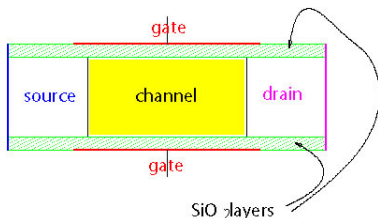


Figure: A **Metal Oxide Semiconductor Field Effect Transistor**.

# Mesoscale Modelling

## Transport.

The Boltzmann Transport Equation (BTE) describes, at mesoscopic level, how the charge carriers move inside the object of study:

$$\frac{\partial f}{\partial t} + \mathbf{v} \cdot \nabla_{\mathbf{x}} f + \frac{\mathbf{F}(t, \mathbf{x})}{m} \cdot \nabla_{\mathbf{v}} f = \mathcal{Q}[f].$$

## Force field.

Apart from the free motion, the charge carriers may be driven by the effect of a force field: self-consistent Poisson equation.

## Collisions.

The charge carriers may have collisions with other carriers, with the fixed lattice or with phonons (pseudo-particles describing the vibration of the lattice).

*J. A. Carrillo, I. Gamba, A. Majorana, C. W. Shu, J. Comp. Phys. 2003 and 2006.*

# Mesoscale Modelling

## Transport.

The Boltzmann Transport Equation (BTE) describes, at mesoscopic level, how the charge carriers move inside the object of study:

$$\frac{\partial f}{\partial t} + v \cdot \nabla_x f + \frac{F(t, x)}{m} \cdot \nabla_v f = Q[f].$$

## Force field.

Apart from the free motion, the charge carriers may be driven by the effect of a force field: self-consistent Poisson equation.

## Collisions.

The charge carriers may have collisions with other carriers, with the fixed lattice or with phonons (pseudo-particles describing the vibration of the lattice).

# Mesoscale Modelling

## Transport.

The Boltzmann Transport Equation (BTE) describes, at mesoscopic level, how the charge carriers move inside the object of study:

$$\frac{\partial f}{\partial t} + v \cdot \nabla_x f + \frac{F(t, x)}{m} \cdot \nabla_v f = Q[f].$$

## Force field.

Apart from the free motion, the charge carriers may be driven by the effect of a force field: self-consistent Poisson equation.

## Collisions.

The charge carriers may have collisions with other carriers, with the fixed lattice or with phonons (pseudo-particles describing the vibration of the lattice).

*J. A. Carrillo, I. Gamba, A. Majorana, C. W. Shu, J. Comp. Phys. 2003 and 2006.*

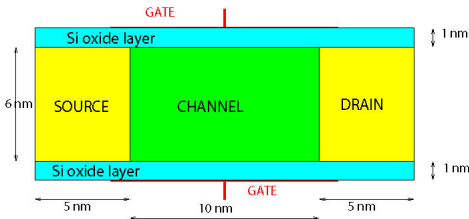
# Outline

- 1 Introduction
  - Introduction
- 2 **NanoMOSFET**
  - **Geometry**
  - Mathematical model
- 3 NM: Kinetic Equations
  - Splitting techniques
  - PWENO interpolations
  - Benchmark tests
- 4 NM: Schrödinger-Poisson
  - Newton-Raphson Algorithms
  - Solvers for Schrödinger and Poisson
- 5 Experiments
  - Results



# The model

We afford the simulation of a nanoscaled MOSFET.



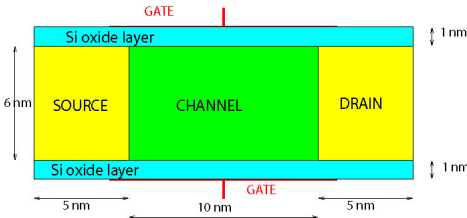
## Dimensional coupling

x-dimension is longer than z-dimension, therefore we adopt a different description:

- along **x-dimension** electrons behave like **particles**, their movement being described by the Boltzmann Transport Equation;
- along **z-dimension** electrons confined in a potential well behave like **waves**, moreover they are supposed to be at equilibrium, therefore their state is given by the stationary-state Schrödinger equation.

# The model

We afford the simulation of a nanoscaled MOSFET.



## Dimensional coupling

x-dimension is longer than z-dimension, therefore we adopt a different description:

- along **x-dimension** electrons behave like **particles**, their movement being described by the Boltzmann Transport Equation;
- along **z-dimension** electrons confined in a potential well behave like **waves**, moreover they are supposed to be at equilibrium, therefore their state is given by the stationary-state Schrödinger equation.

# The model

## Subband decomposition

Electrons in different energy levels, also called *sub-bands*, another name for the **eigenvalues of the Schrödinger equation**, have to be considered independent populations, so that we have to transport them for separate.

## Coupling between dimensions

Dimensions and subbands are coupled in the Poisson equation for the computation of the electrostatic field in the expression of the total density.

## Coupling between subbands

Subbands are also coupled in the scattering operator, where the carriers are allowed to jump from an energy level to another one.

# The model

## Subband decomposition

Electrons in different energy levels, also called *sub-bands*, another name for the **eigenvalues of the Schrödinger equation**, have to be considered independent populations, so that we have to transport them for separate.

## Coupling between dimensions

Dimensions and subbands are coupled in the Poisson equation for the computation of the electrostatic field in the expression of the total density.

## Coupling between subbands

Subbands are also coupled in the scattering operator, where the carriers are allowed to jump from an energy level to another one.

# The model

## Subband decomposition

Electrons in different energy levels, also called *sub-bands*, another name for the **eigenvalues of the Schrödinger equation**, have to be considered independent populations, so that we have to transport them for separate.

## Coupling between dimensions

Dimensions and subbands are coupled in the Poisson equation for the computation of the electrostatic field in the expression of the total density.

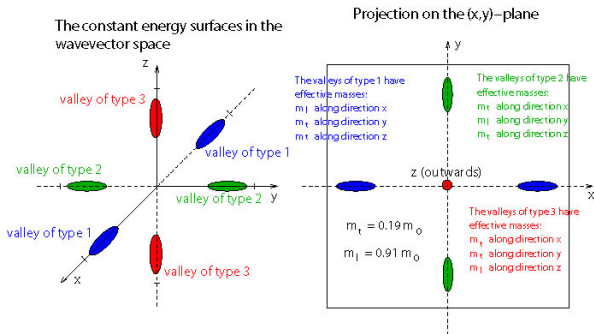
## Coupling between subbands

Subbands are also coupled in the scattering operator, where the carriers are allowed to jump from an energy level to another one.

# Bandstructure

## The three valleys

The Si bandstructure presents six minima in the first Brillouin zone:



The axes of the ellipsoids are disposed along the x, y and z axes of the reciprocal lattice. The three minima have the same value, therefore there is no gap.

# Bandstructure

## Non-parabolicity

The bandstructure around the three minima can be expanded following the Kane non-parabolic approximation:

$$\epsilon_{\nu}^{kin} = \frac{\hbar^2}{1 + \sqrt{1 + 2\tilde{\alpha}_{\nu}\hbar^2 \left( \frac{k_x^2}{m_x^*} + \frac{k_y^2}{m_y^*} \right)}} \left( \frac{k_x^2}{m_x^*} + \frac{k_y^2}{m_y^*} \right),$$

where  $m_{\nu}^{\{x,y\}}$  are the axes of the ellipsoids (called *effective masses*) of the  $\nu^{\text{th}}$  valley along  $x$  and  $y$  directions, and the  $\tilde{\alpha}_{\nu}$  are known as Kane dispersion factors.

The simplest case: one-valley, parabolic

$$\epsilon^{kin} = \frac{\hbar^2 |k|^2}{2m_*},$$

with  $m_*$  an average value between the effective masses.

# Bandstructure

## Non-parabolicity

The bandstructure around the three minima can be expanded following the Kane non-parabolic approximation:

$$\epsilon_{\nu}^{kin} = \frac{\hbar^2}{1 + \sqrt{1 + 2\tilde{\alpha}_{\nu}\hbar^2 \left( \frac{k_x^2}{m_x^2} + \frac{k_y^2}{m_y^2} \right)}} \left( \frac{k_x^2}{m_{\nu}^x} + \frac{k_y^2}{m_{\nu}^y} \right),$$

where  $m_{\nu}^{\{x,y\}}$  are the axes of the ellipsoids (called *effective masses*) of the  $\nu^{\text{th}}$  valley along  $x$  and  $y$  directions, and the  $\tilde{\alpha}_{\nu}$  are known as Kane dispersion factors.

The simplest case: one-valley, parabolic

$$\epsilon^{kin} = \frac{\hbar^2 |k|^2}{2m_*},$$

with  $m_*$  an average value between the effective masses.



# Outline

- 1 Introduction
  - Introduction
- 2 NanoMOSFET
  - Geometry
  - **Mathematical model**
- 3 NM: Kinetic Equations
  - Splitting techniques
  - PWENO interpolations
  - Benchmark tests
- 4 NM: Schrödinger-Poisson
  - Newton-Raphson Algorithms
  - Solvers for Schrödinger and Poisson
- 5 Experiments
  - Results

# The model

## BTE

The Boltzmann Transport Equation (one for each band and for each valley) reads

$$\frac{\partial f_{\nu,p}}{\partial t} + \frac{1}{\hbar} \nabla_k \epsilon_{\nu}^{\text{kin}} \cdot \nabla_x f_{\nu,p} - \frac{1}{\hbar} \nabla_x \epsilon_{\nu,p}^{\text{pot}} \cdot \nabla_k f_{\nu,p} = Q_{\nu,p}[f], \quad f_{\nu,p}(t=0) = \rho_{\nu,p}^{\text{eq}} M.$$

## Schrödinger-Poisson block

$$-\frac{\hbar^2}{2} \frac{d}{dz} \left[ \frac{1}{m_{\nu}} \frac{d\chi_{\nu,p}[V]}{dz} \right] - q(V + V_c) \chi_{\nu,p}[V] = \epsilon_{\nu,p}^{\text{pot}}[V] \chi_{\nu,p}[V]$$

$\{\chi_{\nu,p}\}_p \subseteq H_o^1(0, l_z)$  orthonormal basis in  $L^2(0, l_z)$

$$-\text{div} [\epsilon_R \nabla V] = -\frac{q}{\epsilon_0} \left( \sum_{\nu,p} \rho_{\nu,p} |\chi_{\nu,p}[V]|^2 - N_D \right)$$

plus boundary conditions.

These equations cannot be decoupled because we need the **eigenfunctions** to compute the potential (in the expression of the **total density**), and we need the potential to compute the eigenfunctions.

# The model

## BTE

The Boltzmann Transport Equation (one for each band and for each valley) reads

$$\frac{\partial f_{\nu,p}}{\partial t} + \frac{1}{\hbar} \nabla_k \epsilon_{\nu}^{\text{kin}} \cdot \nabla_x f_{\nu,p} - \frac{1}{\hbar} \nabla_x \epsilon_{\nu,p}^{\text{pot}} \cdot \nabla_k f_{\nu,p} = Q_{\nu,p}[f], \quad f_{\nu,p}(t=0) = \rho_{\nu,p}^{\text{eq}} M.$$

## Schrödinger-Poisson block

$$-\frac{\hbar^2}{2} \frac{d}{dz} \left[ \frac{1}{m_{\nu}} \frac{d\chi_{\nu,p}[V]}{dz} \right] - q(V + V_c) \chi_{\nu,p}[V] = \epsilon_{\nu,p}^{\text{pot}}[V] \chi_{\nu,p}[V]$$

$\{\chi_{\nu,p}\}_p \subseteq H_0^1(0, l_z)$  orthonormal basis in  $L^2(0, l_z)$

$$-\text{div}[\epsilon_R \nabla V] = -\frac{q}{\epsilon_0} \left( \sum_{\nu,p} \rho_{\nu,p} |\chi_{\nu,p}[V]|^2 - N_D \right)$$

plus boundary conditions.

These equations cannot be decoupled because we need the **eigenfunctions** to compute the potential (in the expression of the **total density**), and we need the potential to compute the eigenfunctions.

# The model

## The collision operator

The collision operator takes into account the electron-optical phonon scattering mechanism. It reads

$$Q_{\nu,p}[f] = \sum_s \sum_{\nu',p'} \int_{\mathbb{R}^2} [\mathcal{S}_{(\nu',p',k') \rightarrow (\nu,p,k)}^s f_{\nu',p'}(k') - \mathcal{S}_{(\nu,p,k) \rightarrow (\nu',p',k')}^s f_{\nu,p}(k)] dk' :$$

every  $\mathcal{S}^s$  represents a different interaction, which may be elastic or inelastic, intra-valley or inter-valley. Each of them is inter-band.

## Structure of the $\mathcal{S}^s$

Each of the  $\mathcal{S}^s$  consists of a constant, an overlap integral and a delta for the exchange of energy:

$$\mathcal{S}_{(\nu,p,k) \rightarrow (\nu',p',k')}^s = C_{\nu,\nu'} \int_0^{l_z} |\chi_{\nu,p}|^2 |\chi_{\nu',p'}|^2 dz \delta(\epsilon_{\nu',p'}^{\text{tot}}(k') - \epsilon_{\nu,p}^{\text{tot}}(k) \pm \hbar\omega).$$

# The model

## The collision operator

The collision operator takes into account the electron-optical phonon scattering mechanism. It reads

$$Q_{\nu,p}[f] = \sum_s \sum_{\nu',p'} \int_{\mathbb{R}^2} [\mathcal{S}_{(\nu',p',k') \rightarrow (\nu,p,k)}^s f_{\nu',p'}(k') - \mathcal{S}_{(\nu,p,k) \rightarrow (\nu',p',k')}^s f_{\nu,p}(k)] dk' :$$

every  $S^s$  represents a different interaction, which may be elastic or inelastic, intra-valley or inter-valley. Each of them is inter-band.

## Structure of the $S^s$

Each of the  $S^s$  consists of a constant, an overlap integral and a delta for the exchange of energy:

$$\mathcal{S}_{(\nu,p,k) \rightarrow (\nu',p',k')}^s = C_{\nu,\nu'} \int_0^{l_z} |\chi_{\nu,p}|^2 |\chi_{\nu',p'}|^2 dz \delta(\epsilon_{\nu',p'}^{\text{tot}}(k') - \epsilon_{\nu,p}^{\text{tot}}(k) \pm \hbar\omega).$$

# Outline

- 1 Introduction
  - Introduction
- 2 NanoMOSFET
  - Geometry
  - Mathematical model
- 3 **NM: Kinetic Equations**
  - **Splitting techniques**
  - PWENO interpolations
  - Benchmark tests
- 4 NM: Schrödinger-Poisson
  - Newton-Raphson Algorithms
  - Solvers for Schrödinger and Poisson
- 5 Experiments
  - Results

# Motivation

In this work, splitting techniques are used at different levels, namely:

- to split the Boltzmann Transport Equation into the solution of the **transport part** and the **collisional part** for separate, i.e. the **Time Splitting**:

$$\frac{\partial f}{\partial t} + \mathbf{v} \cdot \nabla_x f + \mathbf{F} \cdot \nabla_v f = \mathcal{Q}[f]$$

splits into

$$\frac{\partial f}{\partial t} + \mathbf{v} \cdot \nabla_x f + \mathbf{F} \cdot \nabla_v f = 0, \quad \frac{\partial f}{\partial t} = \mathcal{Q}[f];$$

- to split the  $(\mathbf{x}, \mathbf{v})$ -phase space in a collisionless context (**Dimensional Splitting**):

$$\frac{\partial f}{\partial t} + \mathbf{v} \cdot \nabla_x f + \mathbf{F} \cdot \nabla_v f = 0$$

splits into

$$\frac{\partial f}{\partial t} + \mathbf{v} \cdot \nabla_x f = 0, \quad \frac{\partial f}{\partial t} + \mathbf{F} \cdot \nabla_v f = 0.$$

# Motivation

In this work, splitting techniques are used at different levels, namely:

- to split the Boltzmann Transport Equation into the solution of the **transport part** and the **collisional part** for separate, i.e. the **Time Splitting**:

$$\frac{\partial f}{\partial t} + \mathbf{v} \cdot \nabla_{\mathbf{x}} f + \mathbf{F} \cdot \nabla_{\mathbf{v}} f = \mathcal{Q}[f]$$

splits into

$$\frac{\partial f}{\partial t} + \mathbf{v} \cdot \nabla_{\mathbf{x}} f + \mathbf{F} \cdot \nabla_{\mathbf{v}} f = 0, \quad \frac{\partial f}{\partial t} = \mathcal{Q}[f];$$

- to split the  $(\mathbf{x}, \mathbf{v})$ -phase space in a collisionless context (**Dimensional Splitting**):

$$\frac{\partial f}{\partial t} + \mathbf{v} \cdot \nabla_{\mathbf{x}} f + \mathbf{F} \cdot \nabla_{\mathbf{v}} f = 0$$

splits into

$$\frac{\partial f}{\partial t} + \mathbf{v} \cdot \nabla_{\mathbf{x}} f = 0, \quad \frac{\partial f}{\partial t} + \mathbf{F} \cdot \nabla_{\mathbf{v}} f = 0.$$



# Motivation

In this work, splitting techniques are used at different levels, namely:

- to split the Boltzmann Transport Equation into the solution of the **transport part** and the **collisional part** for separate, i.e. the **Time Splitting**:

$$\frac{\partial f}{\partial t} + \mathbf{v} \cdot \nabla_{\mathbf{x}} f + \mathbf{F} \cdot \nabla_{\mathbf{v}} f = \mathcal{Q}[f]$$

splits into

$$\frac{\partial f}{\partial t} + \mathbf{v} \cdot \nabla_{\mathbf{x}} f + \mathbf{F} \cdot \nabla_{\mathbf{v}} f = 0, \quad \frac{\partial f}{\partial t} = \mathcal{Q}[f];$$

- to split the  $(\mathbf{x}, \mathbf{v})$ -phase space in a collisionless context (**Dimensional Splitting**):

$$\frac{\partial f}{\partial t} + \mathbf{v} \cdot \nabla_{\mathbf{x}} f + \mathbf{F} \cdot \nabla_{\mathbf{v}} f = 0$$

splits into

$$\frac{\partial f}{\partial t} + \mathbf{v} \cdot \nabla_{\mathbf{x}} f = 0, \quad \frac{\partial f}{\partial t} + \mathbf{F} \cdot \nabla_{\mathbf{v}} f = 0.$$

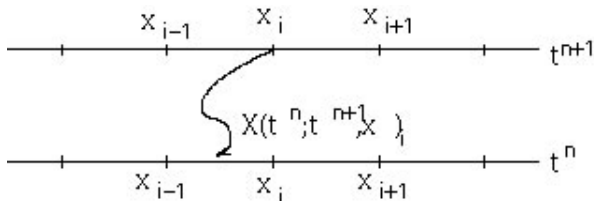
# Linear advection

We propose two schemes for solving the linear advection

$$\frac{\partial f}{\partial t} + v \frac{\partial f}{\partial x} = 0 :$$

Semi-Lagrangian:

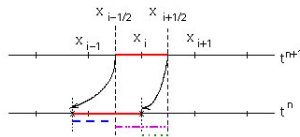
Directly integrate backward in the characteristic



# Linear advection 2

## Flux Balance Method:

Total mass conservation is forced. It is based on the idea of following backward the characteristics, but integral values are taken instead of point values:



The averages along the red segments are the same, because we have followed the characteristics backward.

**FLUX BALANCE METHOD** means evaluating the flux at time  $t^{n+1}$  from a balance of fluxes at previous time  $t^n$  :

----- the average along the purple segment

- - - - - plus the average along the blue segment

..... minus the average along the green segment

# Outline

- 1 Introduction
  - Introduction
- 2 NanoMOSFET
  - Geometry
  - Mathematical model
- 3 **NM: Kinetic Equations**
  - Splitting techniques
  - **PWENO interpolations**
  - Benchmark tests
- 4 NM: Schrödinger-Poisson
  - Newton-Raphson Algorithms
  - Solvers for Schrödinger and Poisson
- 5 Experiments
  - Results

# Motivation

*J.A. Carrillo, F. Vecil, SIAM J. Sci. Computing 2007*

We need a **Pointwise** interpolation method which does not add spurious oscillations when high gradients appear, e.g. when a jump has to be transported.

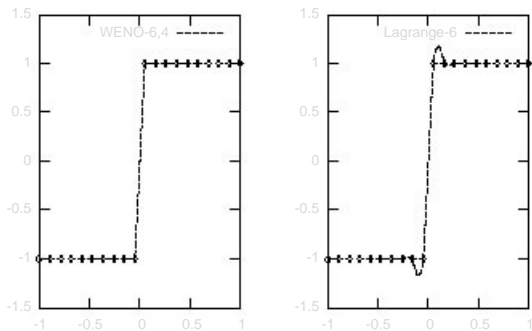


Figure: Left: PWENO interpolation. Right: Lagrange interpolation.

# Motivation

*J.A. Carrillo, F. Vecil, SIAM J. Sci. Computing 2007*

We need a **Pointwise** interpolation method which does not add spurious oscillations when high gradients appear, e.g. when a jump has to be transported.

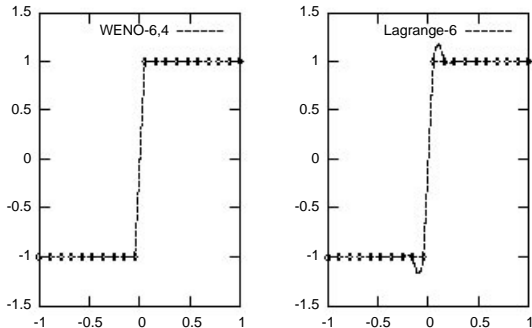
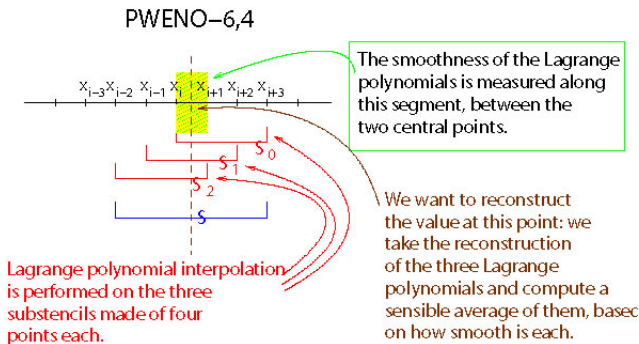


Figure: Left: PWENO interpolation. Right: Lagrange interpolation.

# Non-oscillatory properties

Essentially Non Oscillatory (ENO) methods are based on on a sensible average of Lagrange polynomial reconstructions.

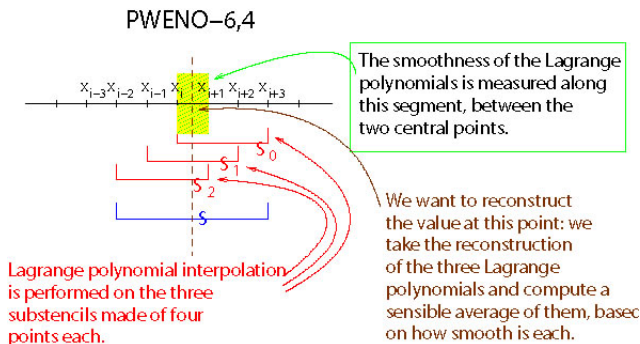
We describe the case of PWENO-6,4: we take a stencil of six points and divide it into three substencils of four points:



# Non-oscillatory properties

Essentially Non Oscillatory (ENO) methods are based on on a sensible average of Lagrange polynomial reconstructions.

We describe the case of PWENO-6,4: we take a stencil of six points and divide it into three substencils of four points:





# Outline

- 1 Introduction
  - Introduction
- 2 NanoMOSFET
  - Geometry
  - Mathematical model
- 3 **NM: Kinetic Equations**
  - Splitting techniques
  - PWENO interpolations
  - **Benchmark tests**
- 4 NM: Schrödinger-Poisson
  - Newton-Raphson Algorithms
  - Solvers for Schrödinger and Poisson
- 5 Experiments
  - Results

# Vlasov with confining potential

We solve a Vlasov equation with **given potential** and a **linear relaxation-time operator** as collision operator by time (linear) splitting to decouple the Vlasov part and the Boltzmann part, and recursively dimensional splitting to divide the  $x$ -advection from the  $v$ -advection:

$$\frac{\partial f}{\partial t} + v \frac{\partial f}{\partial x} - \frac{d\left(\frac{x^2}{2}\right)}{dx} \frac{\partial f}{\partial v} = \frac{1}{\tau} \left[ \frac{1}{\pi} e^{-\frac{v^2}{2}} \rho - f \right], \quad f(0, x) = f_0(x).$$

We expect the solution to rotate (due to the Vlasov part and the potential) and to converge to an **equilibrium** (due to collisions) given by

$$f_s = \frac{\text{mass}(f)}{\pi^2} \exp\left(-\frac{x^2 + v^2}{2}\right).$$

# Setting up initial conditions

We perform tests with two initial conditions, more or less close to the equilibrium; the relaxation time is set  $\tau = 3.5$ :

$$f_0^{(1)} = Z_1 \sin^2 \left( \frac{X}{2} \right) e^{-\frac{x^2+v^2}{2}}$$

$$f_0^{(2)} = Z_2 \sin^2 \left( \frac{X}{2} \right) \sin^2 \left( \frac{V}{2} \right) e^{-\frac{x^2+v^2}{2}}$$

## Entropies

The **global** and **local** relative entropies are defined this way:

$$H[f; f_s] = \int_{\mathbb{R}} \int_{\mathbb{R}} \frac{|f - f_s|^2}{f_s} dv dx$$
$$\tilde{H}[f; \rho M_1] = \int_{\mathbb{R}} \int_{\mathbb{R}} \frac{|f - \rho M_1|^2}{f_s} dv dx.$$

# Vlasov-Poisson: Two-stream instability

## The problem

We set the problem in a collision-less context. The **force field** is self-consistently computed through a **Poisson equation**. Equations are normalized, periodic boundary conditions are taken for both the transport and the potential.

$$\frac{\partial f}{\partial t} + v \frac{\partial f}{\partial x} - \frac{\partial \Phi}{\partial x} \frac{\partial f}{\partial v} = 0$$

$$\frac{\partial^2 \Phi}{\partial x^2} = 1 - \int_{\mathbb{R}} f dv$$

$$f(t=0, x, v) = f_{eq}(v) \left[ 1 + 0.01 \left( \frac{\cos(2kx) + \cos(3kx)}{1.2} + \cos(kx) \right) \right].$$

As **initial condition**, we perturb the equilibrium-state given by

$$f_{eq}(v) = K(1 + v^2)e^{-\frac{v^2}{2}},$$

$K$  being a normalization factor.

# Outline

- 1 Introduction
  - Introduction
- 2 NanoMOSFET
  - Geometry
  - Mathematical model
- 3 NM: Kinetic Equations
  - Splitting techniques
  - PWENO interpolations
  - Benchmark tests
- 4 **NM: Schrödinger-Poisson**
  - **Newton-Raphson Algorithms**
  - Solvers for Schrödinger and Poisson
- 5 Experiments
  - Results

# The Newton scheme

## The PDE to solve

Solving the Schrödinger-Poisson block

$$-\frac{\hbar^2}{2} \frac{d}{dz} \left[ \frac{1}{m_\nu} \frac{d\chi_{\nu,p}[V]}{dz} \right] - q(V + V_c) \chi_{\nu,p}[V] = \epsilon_{\nu,p}^{\text{pot}}[V] \chi_{\nu,p}[V]$$

$$-\text{div}[\epsilon_R \nabla V] = -\frac{q}{\epsilon_0} \left( \sum_{\nu,p} \rho_{\nu,p} |\chi_{\nu,p}[V]|^2 - N_D \right)$$

is equivalent to minimizing, under the constraints of the Schrödinger equation, the functional associated to  $P[V]$

$$P[V] = -\text{div}(\epsilon_R \nabla V) + \frac{q}{\epsilon_0} \left( \sum_{\nu,p} \rho_{\nu,p} |\chi_{\nu,p}[V]|^2 - N_D \right),$$

## The scheme

which is achieved by means of a Newton scheme

$$dP(V^{\text{old}}, V^{\text{new}} - V^{\text{old}}) = -P[V^{\text{old}}].$$

# The Newton scheme

## The PDE to solve

Solving the Schrödinger-Poisson block

$$-\frac{\hbar^2}{2} \frac{d}{dz} \left[ \frac{1}{m_\nu} \frac{d\chi_{\nu,p}[V]}{dz} \right] - q(V + V_c) \chi_{\nu,p}[V] = \epsilon_{\nu,p}^{\text{pot}}[V] \chi_{\nu,p}[V]$$

$$-\text{div} [\epsilon_R \nabla V] = -\frac{q}{\epsilon_0} \left( \sum_{\nu,p} \rho_{\nu,p} |\chi_{\nu,p}[V]|^2 - N_D \right)$$

is equivalent to minimizing, under the constraints of the Schrödinger equation, the functional associated to  $P[V]$

$$P[V] = -\text{div} (\epsilon_R \nabla V) + \frac{q}{\epsilon_0} \left( \sum_{\nu,p} \rho_{\nu,p} |\chi_{\nu,p}[V]|^2 - N_D \right),$$

## The scheme

which is achieved by means of a Newton scheme

$$dP(V^{\text{old}}, V^{\text{new}} - V^{\text{old}}) = -P[V^{\text{old}}].$$

# The iterations

## Derivatives

The Gâteaux-derivatives of the eigenproperties are needed:

$$d\epsilon_{\nu,p}(V, U) = -q \int U(\zeta) |\chi_{\nu,p}[V](\zeta)|^2 d\zeta$$

$$d\chi_{\nu,p}(V, U) = -q \sum_{p' \neq p} \frac{\int U(\zeta) \chi_{\nu,p}[V](\zeta) \chi_{\nu,p'}[V](\zeta) d\zeta}{\epsilon_{\nu,p}[V] - \epsilon_{\nu,p'}[V]} \chi_{\nu,p'}[V](z).$$

## Iterations

After computing the Gâteaux-derivative of the density and developing calculations, we are led to a Poisson-like equation

$$\begin{aligned} & -\operatorname{div}(\epsilon_R \nabla V^{\text{new}}) + \int_0^{Lz} \mathcal{A}[V^{\text{old}}](z, \zeta) V^{\text{new}}(\zeta) d\zeta \\ &= -\frac{q}{\epsilon_0} (N[V^{\text{old}}] - N_D) + \int_0^{Lz} \mathcal{A}[V^{\text{old}}](z, \zeta) V^{\text{old}}(\zeta) d\zeta, \end{aligned}$$

where  $\mathcal{A}[V]$  is essentially the Gâteaux-derivative of the functional  $P[V]$ .



# The iterations

## Derivatives

The Gâteaux-derivatives of the eigenproperties are needed:

$$d\epsilon_{\nu,p}(V, U) = -q \int U(\zeta) |\chi_{\nu,p}[V](\zeta)|^2 d\zeta$$

$$d\chi_{\nu,p}(V, U) = -q \sum_{p' \neq p} \frac{\int U(\zeta) \chi_{\nu,p}[V](\zeta) \chi_{\nu,p'}[V](\zeta) d\zeta}{\epsilon_{\nu,p}[V] - \epsilon_{\nu,p'}[V]} \chi_{\nu,p'}[V](z).$$

## Iterations

After computing the Gâteaux-derivative of the density and developing calculations, we are led to a Poisson-like equation

$$\begin{aligned} & -\operatorname{div}(\epsilon_R \nabla V^{\text{new}}) + \int_0^{Lz} \mathcal{A}[V^{\text{old}}](z, \zeta) V^{\text{new}}(\zeta) d\zeta \\ &= -\frac{q}{\epsilon_0} (N[V^{\text{old}}] - N_D) + \int_0^{Lz} \mathcal{A}[V^{\text{old}}](z, \zeta) V^{\text{old}}(\zeta) d\zeta, \end{aligned}$$

where  $\mathcal{A}[V]$  is essentially the Gâteaux-derivative of the functional  $P[V]$ .

# Outline

- 1 Introduction
  - Introduction
- 2 NanoMOSFET
  - Geometry
  - Mathematical model
- 3 NM: Kinetic Equations
  - Splitting techniques
  - PWENO interpolations
  - Benchmark tests
- 4 NM: Schrödinger-Poisson
  - Newton-Raphson Algorithms
  - Solvers for Schrödinger and Poisson
- 5 Experiments
  - Results

# Numerical methods

## The Schrödinger equation

### Equation

$$-\frac{\hbar^2}{2} \frac{d}{dz} \left[ \frac{1}{m_\nu} \frac{d\chi_{\nu,p}}{dz} \right] - q(V + V_c) \chi_{\nu,p} = \epsilon_{\nu,p} \chi_{\nu,p}$$

is discretized by alternate finite differences for the derivatives then the symmetric matrix is diagonalized by a LAPACK routine called DSTEQR.

## The Poisson equation

We need to solve equations like

$$-\text{div} [\epsilon_R \nabla V] + \int_0^{l_z} \mathcal{A}(z, \zeta) V(\zeta) d\zeta = B(z).$$

The derivatives are discretized by finite differences in alternate directions, the integral is computed via trapezoid rule and the linear system (full) is solved by means of a LAPACK routine called DGESV.

# Numerical methods

## The Schrödinger equation

### Equation

$$-\frac{\hbar^2}{2} \frac{d}{dz} \left[ \frac{1}{m_\nu} \frac{d\chi_{\nu,p}}{dz} \right] - q(V + V_c) \chi_{\nu,p} = \epsilon_{\nu,p} \chi_{\nu,p}$$

is discretized by alternate finite differences for the derivatives then the symmetric matrix is diagonalized by a LAPACK routine called DSTEQR.

## The Poisson equation

We need to solve equations like

$$-\text{div} [\epsilon_R \nabla V] + \int_0^{l_z} \mathcal{A}(z, \zeta) V(\zeta) d\zeta = \mathcal{B}(z).$$

The derivatives are discretized by finite differences in alternate directions, the integral is computed via trapezoid rule and the linear system (full) is solved by means of a LAPACK routine called DGESV.

# Three Schrödinger-Poisson Problems

## Boundary potential

$V_{bp}(0) = V_{bp}(L_z) = 0$  and

$$N[V_{bp}](0, z) = \frac{\int_0^{L_z} N_D(0, \zeta) d\zeta}{\mathcal{Z}[V_{bp}](0)} \sum_{p=1}^{\infty} e^{-\frac{\epsilon_p[V_{bp}](0)}{k_B T_L}} |\chi_p[V_{bp}](0, z)|^2,$$

where the repartition function has the general expression:

$$\mathcal{Z}[V](x) = \sum_{q=1}^{\infty} e^{-\frac{\epsilon_q[V](x)}{k_B T_L}}.$$

## The Thermodynamical equilibrium

$$N[V_{eq}] = \frac{\int_0^{L_z} N_D(0, \zeta) d\zeta}{\mathcal{Z}[V_{bp}](0)} \sum_{p=1}^{\infty} e^{-\frac{\epsilon_p[V_{eq}](x)}{k_B T_L}} |\chi_p[V_{eq}](x, z)|^2.$$

# Three Schrödinger-Poisson Problems

## Boundary potential

$V_{bp}(0) = V_{bp}(L_z) = 0$  and

$$N[V_{bp}](0, z) = \frac{\int_0^{L_z} N_D(0, \zeta) d\zeta}{\mathcal{Z}[V_{bp}](0)} \sum_{p=1}^{\infty} e^{-\frac{\epsilon_p[V_{bp}](0)}{k_B T_L}} |\chi_p[V_{bp}](0, z)|^2,$$

where the repartition function has the general expression:

$$\mathcal{Z}[V](x) = \sum_{q=1}^{\infty} e^{-\frac{\epsilon_q[V](x)}{k_B T_L}}.$$

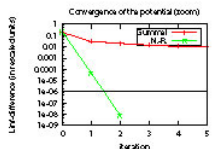
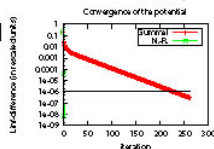
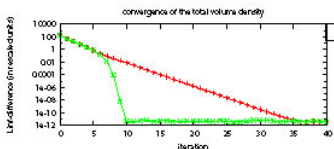
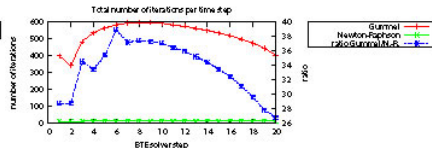
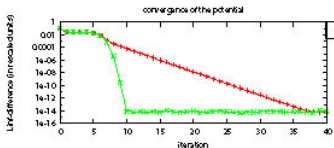
## The Thermodynamical equilibrium

$$N[V_{eq}] = \frac{\int_0^{L_z} N_D(0, \zeta) d\zeta}{\mathcal{Z}[V_{bp}](0)} \sum_{p=1}^{\infty} e^{-\frac{\epsilon_p[V_{eq}](x)}{k_B T_L}} |\chi_p[V_{eq}](x, z)|^2.$$

# Efficiency versus Gummel

## Gummel iteration

$$-\text{div}(\epsilon_R \nabla V^{new}) + \frac{q}{\epsilon_0} N[V^{old}] \frac{q}{k_B T_L} (V^{new} - V^{old}) = -\frac{q}{\epsilon_0} (N[V^{old}] - N_D),$$



# Outline

- 1 Introduction
  - Introduction
- 2 NanoMOSFET
  - Geometry
  - Mathematical model
- 3 NM: Kinetic Equations
  - Splitting techniques
  - PWENO interpolations
  - Benchmark tests
- 4 NM: Schrödinger-Poisson
  - Newton-Raphson Algorithms
  - Solvers for Schrödinger and Poisson
- 5 Experiments
  - Results



# Collision operator

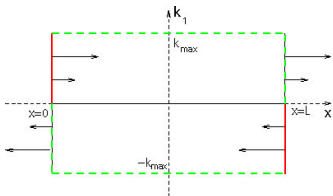
Results are presented for the the DG MOSFET in the one-valley, parabolic-band approximation. Moreover, the complete collision operator is substituted by a simple relaxation-time operator:



$$\mathcal{Q}_p f = \frac{1}{\tau} (\rho_p M - f_p).$$

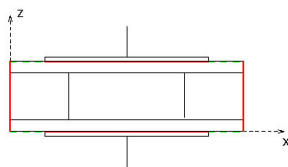
The goal of this work is just the setting up of numerical tools for a more profound and realistic simulation.



A parallel code in the most realistic case is being implemented.

# Boundary Conditions



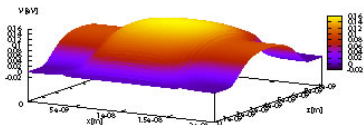
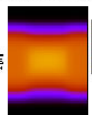
-  = force the density to stay close to the equilibrium density
-  = Homogeneous Neumann



-  = Dirichlet
-  = homogeneous Neumann

# Thermodynamical equilibrium: one-valley case

Potential at equilibrium

1-4h band  $\chi^2 F^2 [n^2(-1)]$ 

x [m]

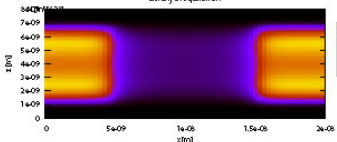
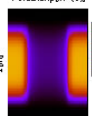
2-4h band  $\chi^2 F^2 [n^2(-1)]$ 

x [m]

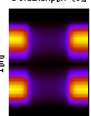
3-4h band  $\chi^2 F^2 [n^2(-1)]$ 

x [m]

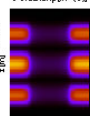
Density at equilibrium

1-4h band  $n_p [n^2(-3)]$ 

x [m]

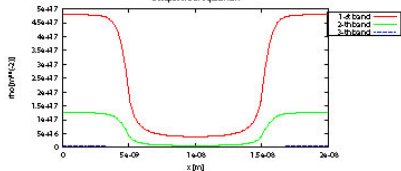
2-4h band  $n_p [n^2(-3)]$ 

x [m]

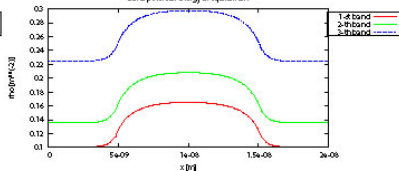
3-4h band  $n_p [n^2(-3)]$ 

x [m]

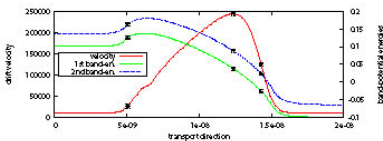
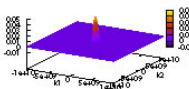
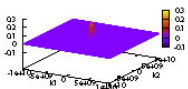
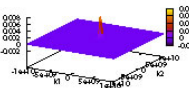
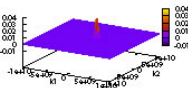
Occupational equilibrium



Band potential energy at equilibrium



# Transient states

1st band-pot at  $x = 5.07965e-09$ 2nd band-pot at  $x = 5.07996e-09$ 1st band-pot at  $x = 1.238095e-08$ 2nd band-pot at  $x = 1.238095e-08$ 1st band-pot at  $x = 1.42871e-08$ 2nd band-pot at  $x = 1.42871e-08$ 